

Data Sheet Issue:- P2

Phase Control Thyristor Types N0465WN140 to N0465WN160

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V _{DRM}	Repetitive peak off-state voltage, (note 1)	1400-1600	V
V _{DSM}	Non-repetitive peak off-state voltage, (note 1)	1500-1700	V
V _{RRM}	Repetitive peak reverse voltage, (note 1)	1400-1600	V
V _{RSM}	Non-repetitive peak reverse voltage, (note 1)	1500-1700	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS		
I _{T(AV)M}	Maximum average on-state current, T _{sink} =55°C, (n	465	А		
I _{T(AV)M}	Maximum average on-state current. T _{sink} =85°C, (n	315	А		
I _{T(AV)M}	Maximum average on-state current. T _{sink} =85°C, (n	180	А		
I _{T(RMS)M}	Nominal RMS on-state current, T _{sink} =25°C, (note 2	920	А		
I _{T(d.c.)}	D.C. on-state current, T _{sink} =25°C, (note 4)	790	А		
I _{TSM}	Peak non-repetitive surge $t_p=10ms$, $V_{rm}=60\% V_{RRM}$	4500	А		
I _{TSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{rm}\leq 10V$, (not	5000	А		
l ² t	$I^{2}t$ capacity for fusing t _p =10ms, V _{rm} =60%V _{RRM} , (no	101×10 ³	A ² s		
l ² t	$I^{2}t$ capacity for fusing t _p =10ms, V _m ≤10V, (note 5)	125×10 ³	A ² s		
		(continuous, 50Hz)	75	A/µs	
(di/dt) _{cr}	Critical rate of rise of on-state current (note 6)	(repetitive, 50Hz, 60s)	125		
		(non-repetitive)	250		
V _{RGM}	Peak reverse gate voltage	5	V		
P _{G(AV)}	Mean forward gate power	3	W		
P _{GM}	Peak forward gate power	30	W		
T _{j op}	Operating temperature range	-60 to +125	°C		
T _{stg}	Storage temperature range	-60 to +125	°C		

Notes:-

1) De-rating factor of 0.13% per °C is applicable for T_i below 25°C.

2) Double side cooled, single phase; 50Hz, 180° half-sinewave.

3) Anode side cooled, single phase; 50Hz, 180° half-sinewave.

4) Double side cooled.

5) Half-sinewave, $125^{\circ}C T_{j}$ initial.

6) $V_D=67\% V_{DRM}$, $I_{TM}=600Å$, $I_{FG}=2A$, $t_r \le 0.5 \mu s$, $T_{case}=125^{\circ}C$.



Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V _{TM}	Maximum peak on-state voltage	-	-	1.30	I _{TM} =465A	V
V _{T0}	Threshold voltage	-	-	0.90		V
r _T	Slope resistance	-	-	0.85		mΩ
(dv/dt) _{cr}	Critical rate of rise of off-state voltage	1000	-	-	V_D =67% V_{DRM} , linear ramp, gate o/c	V/µs
I _{DRM}	Peak off-state current	-	-	50	Rated V _{DRM}	mA
I _{RRM}	Peak reverse current	-	-	50	Rated V _{RRM}	mA
V _{GT}	Gate trigger voltage	-	-	2.50		V
I _{GT}	Gate trigger current	-	-	250	$T_j=25^{\circ}C$ $V_D=10V, I_T=3A$	mA
V_{GD}	Gate non-trigger voltage	-	-	0.25	Rated V _{DRM}	V
I _H	Holding current	-	-	250	T _j =25°C	mA
t _{gd}	Gate-controlled turn-on delay time	-	-	2.0	V _D =67% V _{DRM} , I _T =300A, di/dt=10A/µs, I _{FG} =2A, t _i =0.5µs, T _i =25°C	μs
t _q	Turn-off time	-	-	125	I _{TM} =300A, t _p =500μs, di/dt=10A/μs, V _r =100V, V _{dr} =67%V _{DRM} , dV _{dr} /dt=50V/μs	μs
		-	-	0.080	Double side cooled	K/W
R _{thJK}	Thermal resistance, junction to heatsink	-	-	0.174	Anode side cooled	K/W
		-	-	0.146	Cathode side cooled	K/W
F	Mounting force	5	-	7	Note 2.	kN
W _t	Weight	-	70	-		g

Notes:-

1) Unless otherwise indicated $T_j=125^{\circ}C$.

2) For other clamp forces, please consult factory.



Outline Drawing & Ordering Information

